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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

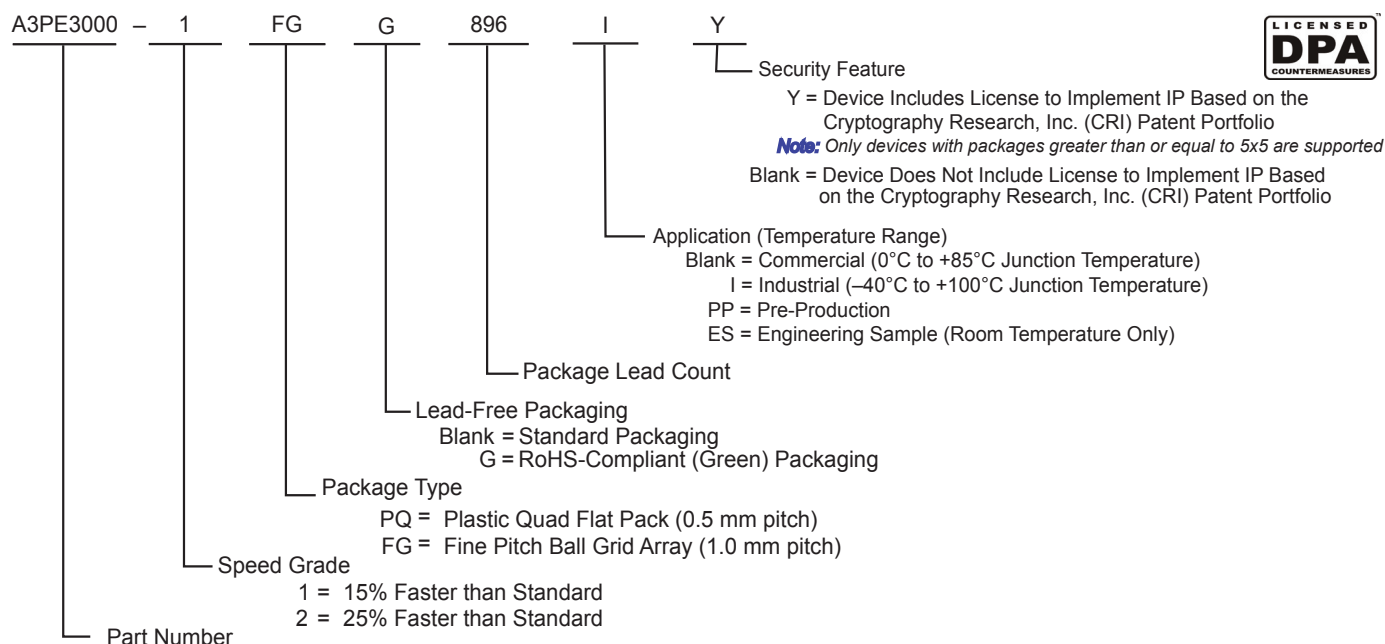
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	221
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	324-BGA
Supplier Device Package	324-FBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000-2fgg324i

ProASIC3E Ordering Information



ProASIC3E Devices

A3PE600 = 600,000 System Gates
A3PE1500 = 1,500,000 System Gates
A3PE3000 = 3,000,000 System Gates

ProASIC3E Devices with Cortex-M1

M1A3PE1500 = 1,500,000 System Gates
M1A3PE3000 = 3,000,000 System Gates

Temperature Grade Offerings

Package	A3PE600	A3PE1500	A3PE3000
Cortex-M1 Devices		M1A3PE1500	M1A3PE3000
PQ208	C, I	C, I	C, I
FG256	C, I	–	–
FG324	–	–	C, I
FG484	C, I	C, I	C, I
FG676	–	C, I	–
FG896	–	–	C, I

Note: C = Commercial temperature range: 0°C to 70°C ambient temperature
 I = Industrial temperature range: –40°C to 85°C ambient temperature

Speed Grade and Temperature Grade Matrix

Temperature Grade	Std.	–1	–2
C ¹	✓	✓	✓
I ²	✓	✓	✓

Notes:

1. C = Commercial temperature range: 0°C to 70°C ambient temperature
2. I = Industrial temperature range: –40°C to 85°C ambient temperature

References made to ProASIC3E devices also apply to ARM-enabled ProASIC3E devices. The ARM-enabled part numbers start with M1 (Cortex-M1).

Contact your local Microsemi SoC Products Group representative for device availability:
www.microsemi.com/index.php?option=com_content&id=135&lang=en&view=article.

Specify I/O States During Programming

Load from file... Save to file... ☐ Show BSR Details

	Port Name	Macro Cell	Pin Number	I/O State (Output Only)
	BIST	ADLIB:INBUF	T2	1
	BYPASS_IO	ADLIB:INBUF	K1	1
	CLK	ADLIB:INBUF	B1	1
	ENOUT	ADLIB:INBUF	J16	1
	LED	ADLIB:OUTBUF	M3	0
	MONITOR[0]	ADLIB:OUTBUF	B5	0
	MONITOR[1]	ADLIB:OUTBUF	C7	Z
	MONITOR[2]	ADLIB:OUTBUF	D9	Z
	MONITOR[3]	ADLIB:OUTBUF	D7	Z
	MONITOR[4]	ADLIB:OUTBUF	A11	Z
	OEa	ADLIB:INBUF	E4	Z
	OEb	ADLIB:INBUF	F1	Z
	OSC_EN	ADLIB:INBUF	K3	Z
	PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
	PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
	PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
	PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
	PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

Help OK Cancel

Figure 1-3 • I/O States During Programming Window

- Click OK to return to the FlashPoint – Programming File Generator window.
I/O States during programming are saved to the ADB and resulting programming files after completing programming file generation.

Table 2-4 • Overshoot and Undershoot Limits¹

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at 85°C.
2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
3. This table does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC[®]3E device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-1 on page 2-4](#).

There are five regions to consider during power-up.

ProASIC3E I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-1 on page 2-4](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.2 V

Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.1 V

Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% as all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = $(100\% + 50\% + 25\% + 12.5\% + \dots + 0.78125\%) / 8$

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-11 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-12 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings
–2 Speed Grade, Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 3.0\text{ V}$

I/O Standard	Drive Strength (mA)	Equivalent Software Default Drive Strength Option) ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PYS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)
3.3 V LVTTTL / 3.3 V LVCMOS	12	12	High	35	–	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81
3.3 V LVCMOS Wide Range ²	100 μA	12	High	35	–	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79
2.5 V LVCMOS	12	12	High	35	–	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28
1.8 V LVCMOS	12	12	High	35	–	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98
1.5 V LVCMOS	12	12	High	35	–	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37
3.3 V PCI	Per PCI spec	–	High	10	25 ³	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 ³	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V GTL	20 ⁴	–	High	10	25	0.45	1.55	0.03	2.19	–	0.32	1.52	1.55	–	–	3.19	3.22
2.5 V GTL	20 ⁴	–	High	10	25	0.45	1.59	0.03	1.83	–	0.32	1.61	1.59	–	–	3.28	3.26
3.3 V GTL+	35	–	High	10	25	0.45	1.53	0.03	1.19	–	0.32	1.56	1.53	–	–	3.23	3.20
2.5 V GTL+	33	–	High	10	25	0.45	1.65	0.03	1.13	–	0.32	1.68	1.57	–	–	3.35	3.24
HSTL (I)	8	–	High	20	50	0.49	2.37	0.03	1.59	–	0.32	2.42	2.35	–	–	4.09	4.02
HSTL (II)	15 ⁴	–	High	20	25	0.49	2.26	0.03	1.59	–	0.32	2.30	2.03	–	–	3.97	3.70
SSTL2 (I)	15	–	High	30	50	0.49	1.59	0.03	1.00	–	0.32	1.62	1.38	–	–	3.29	3.05
SSTL2 (II)	18	–	High	30	25	0.49	1.62	0.03	1.00	–	0.32	1.65	1.32	–	–	3.32	2.99
SSTL3 (I)	14	–	High	30	50	0.49	1.72	0.03	0.93	–	0.32	1.75	1.37	–	–	3.42	3.04
SSTL3 (II)	21	–	High	30	25	0.49	1.54	0.03	0.93	–	0.32	1.57	1.25	–	–	3.24	2.92
LVDS/B-LVDS/M-LVDS	24	–	High	–	–	0.49	1.40	0.03	1.36	–	–	–	–	–	–	–	–
LVPECL	24	–	High	–	–	0.49	1.36	0.03	1.22	–	–	–	–	–	–	–	–

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3V wide range as specified in the JESD8b specification.
3. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-38](#) for connectivity. This resistor is not required during normal operation.
4. Output drive strength is below JEDEC specification.
5. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#).

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer. The 3.3 V LVCMOS standard is supported as part of the 3.3 V LVTTTL support.

Table 2-25 • Minimum and Maximum DC Input and Output Levels

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min., V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

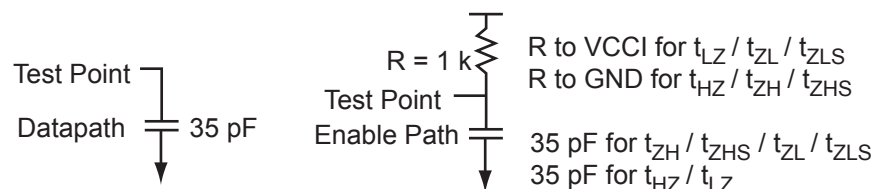


Figure 2-6 • AC Loading

Table 2-26 • 3.3 V LVTTTL / 3.3 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	3.3	1.4	–	35

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Table 2-28 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
12 mA	Std.	0.66	6.03	0.04	1.20	1.57	0.43	6.14	5.02	3.28	3.47	8.37	7.26	ns
	–1	0.56	5.13	0.04	1.02	1.33	0.36	5.22	4.27	2.79	2.95	7.12	6.17	ns
	–2	0.49	4.50	0.03	0.90	1.17	0.32	4.58	3.75	2.45	2.59	6.25	5.42	ns
16 mA	Std.	0.66	5.62	0.04	1.20	1.57	0.43	5.72	4.72	3.32	3.58	7.96	6.96	ns
	–1	0.56	4.78	0.04	1.02	1.33	0.36	4.87	4.02	2.83	3.04	6.77	5.92	ns
	–2	0.49	4.20	0.03	0.90	1.17	0.32	4.27	3.53	2.48	2.67	5.94	5.20	ns
24 mA	Std.	0.66	5.24	0.04	1.20	1.57	0.43	5.34	4.69	3.39	3.96	7.58	6.93	ns
	–1	0.56	4.46	0.04	1.02	1.33	0.36	4.54	3.99	2.88	3.37	6.44	5.89	ns
	–2	0.49	3.92	0.03	0.90	1.17	0.32	3.99	3.50	2.53	2.96	5.66	5.17	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

3.3 V LVCMOS Wide Range

Table 2-29 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	Max. mA ⁴	Max. mA ⁴	μA ⁵	μA ⁵
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	27	25	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	27	25	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	54	51	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	54	51	10	10
100 μA	12 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	109	103	10	10
100 μA	16 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	127	132	10	10
100 μA	24 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	181	268	10	10

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where −0.3 V < VIN < VIL.
3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.
4. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

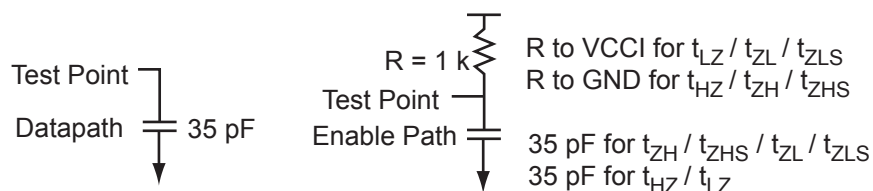


Figure 2-7 • AC Loading

Table 2-30 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	3.3	1.4	–	35

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	4 mA	Std.	0.66	17.02	0.04	1.83	2.38	0.43	17.02	13.74	4.16	3.78	20.42	17.14	ns
		–1	0.56	14.48	0.04	1.55	2.02	0.36	14.48	11.69	3.54	3.21	17.37	14.58	ns
		–2	0.49	12.71	0.03	1.36	1.78	0.32	12.71	10.26	3.11	2.82	15.25	12.80	ns
100 μA	8 mA	Std.	0.66	12.16	0.04	1.83	2.38	0.43	12.16	9.78	4.70	4.74	15.55	13.17	ns
		–1	0.56	10.34	0.04	1.55	2.02	0.36	10.34	8.32	4.00	4.03	13.23	11.20	ns
		–2	0.49	9.08	0.03	1.36	1.78	0.32	9.08	7.30	3.51	3.54	11.61	9.84	ns
100 μA	12 mA	Std.	0.66	9.32	0.04	1.83	2.38	0.43	9.32	7.62	5.06	5.36	12.71	11.02	ns
		–1	0.56	7.93	0.04	1.55	2.02	0.36	7.93	6.48	4.31	4.56	10.81	9.37	ns
		–2	0.49	6.96	0.03	1.36	1.78	0.32	6.96	5.69	3.78	4.00	9.49	8.23	ns
100 μA	16 mA	Std.	0.66	8.69	0.04	1.83	2.38	0.43	8.69	7.17	5.14	5.53	12.08	10.57	ns
		–1	0.56	7.39	0.04	1.55	2.02	0.36	7.39	6.10	4.37	4.71	10.28	8.99	ns
		–2	0.49	6.49	0.03	1.36	1.78	0.32	6.49	5.36	3.83	4.13	9.02	7.89	ns
100 μA	24 mA	Std.	0.66	8.11	0.04	1.83	2.38	0.43	8.11	7.13	5.23	6.13	11.50	10.52	ns
		–1	0.56	6.90	0.04	1.55	2.02	0.36	6.90	6.06	4.45	5.21	9.78	8.95	ns
		–2	0.49	6.05	0.03	1.36	1.78	0.32	6.05	5.32	3.91	4.57	8.59	7.86	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

HSTL Class I

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). ProASIC3E devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-60 • Minimum and Maximum DC Input and Output Levels

HSTL Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
8 mA	−0.3	VREF − 0.1	VREF + 0.1	3.6	0.4	VCCI − 0.4	8	8	39	32	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.

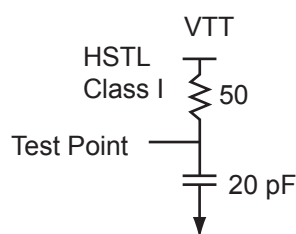


Figure 2-16 • AC Loading

Table 2-61 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-62 • HSTL Class I

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = .4 V, VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.66	3.18	0.04	2.12	0.43	3.24	3.14			5.47	5.38	ns
−1	0.56	2.70	0.04	1.81	0.36	2.75	2.67			4.66	4.58	ns
−2	0.49	2.37	0.03	1.59	0.32	2.42	2.35			4.09	4.02	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Input Register

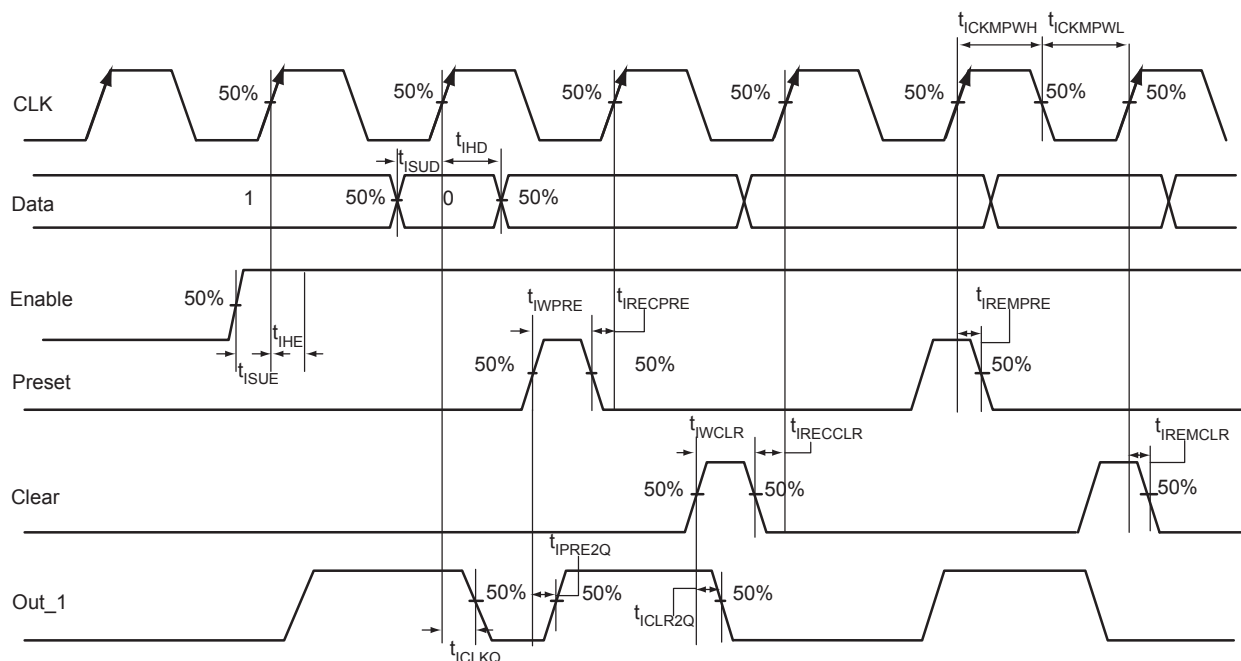


Figure 2-27 • Input Register Timing Diagram

Timing Characteristics

Table 2-86 • Input Data Register Propagation Delays

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IEMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
t_{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

3 – Pin Descriptions and Packaging

Supply Pins

GND**Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ**Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC**Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx**I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground through any resistor and the corresponding VCCIX grounded, then the leakage current to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it's better to float VCCIX of unused bank or tie it to GND.

VMVx**I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F**PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the [ProASIC3E FPGA Fabric User's Guide](#) for a complete board solution for the PLL analog power supply and ground.

There are six VCCPLX pins on ProASIC3E devices.

VCOMPLA/B/C/D/E/F**PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There are six VCOMPL pins (PLL ground) on ProASIC3E devices.

VJTAG

JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

VPUMP

Programming Supply Voltage

For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in the datasheet.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 μ F and 0.33 μ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

User-Defined Supply Pins

VREF

I/O Voltage Reference

Reference voltage for I/O minibanks. VREF pins are configured by the user from regular I/Os, and any I/O in a bank, except JTAG I/Os, can be designated the voltage reference I/O. Only certain I/O standards require a voltage reference—HSTL (I) and (II), SSTL2 (I) and (II), SSTL3 (I) and (II), and GTL/GTL+. One VREF pin can support the number of I/Os available in its minibank.

User Pins

I/O

User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

GL

Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *ProASIC3E FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Special Function Pins

NC

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

No Connect

DC

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Do Not Connect

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

User's Guides

ProASIC3E FPGA Fabric User's Guide

http://www.microsemi.com/document-portal/doc_download/130883-proasic3e-fpga-fabric-user-s-guide

Packaging

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

http://www.microsemi.com/document-portal/doc_download/131095-package-mechanical-drawings

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

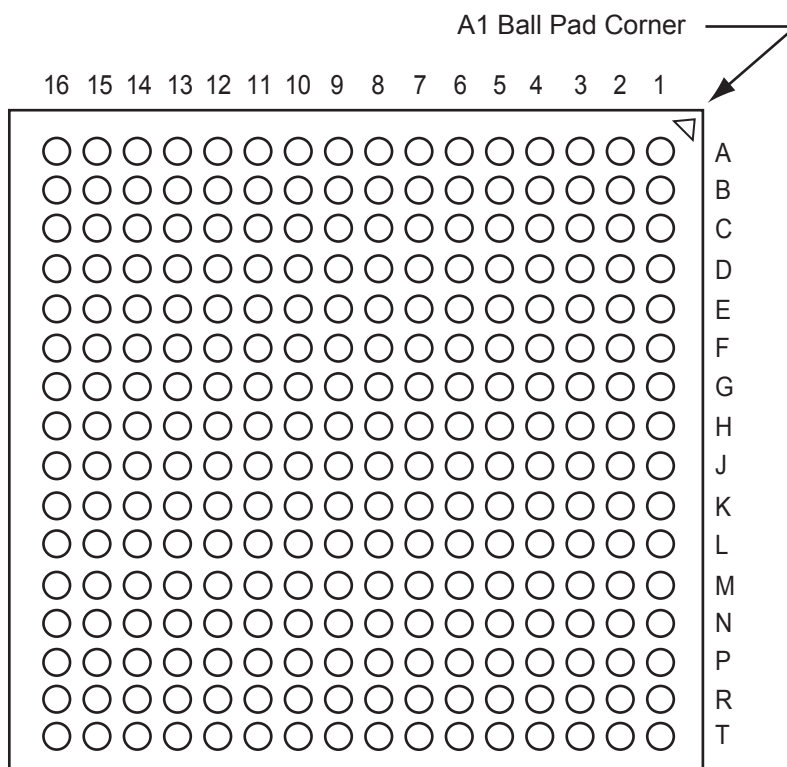
Additional packaging materials: <http://www.microsemi.com/products/fpga-soc/solutions>.

PQ208	
Pin Number	A3PE600 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO133PSB7V1
5	GAA2/IO134PDB7V1
6	IO134NDB7V1
7	GAC2/IO132PDB7V1
8	IO132NDB7V1
9	IO130PDB7V1
10	IO130NDB7V1
11	IO127PDB7V1
12	IO127NDB7V1
13	IO126PDB7V0
14	IO126NDB7V0
15	IO124PSB7V0
16	VCC
17	GND
18	VCCIB7
19	IO122PPB7V0
20	IO121PSB7V0
21	IO122NPB7V0
22	GFC1/IO120PSB7V0
23	GFB1/IO119PDB7V0
24	GFB0/IO119NDB7V0
25	VCOMPLF
26	GFA0/IO118NPB6V1
27	VCCPLF
28	GFA1/IO118PPB6V1
29	GND
30	GFA2/IO117PDB6V1
31	IO117NDB6V1
32	GFB2/IO116PPB6V1
33	GFC2/IO115PPB6V1
34	IO116NPB6V1
35	IO115NPB6V1
36	VCC

PQ208	
Pin Number	A3PE600 Function
37	IO112PDB6V1
38	IO112NDB6V1
39	IO108PSB6V0
40	VCCIB6
41	GND
42	IO106PDB6V0
43	IO106NDB6V0
44	GEC1/IO104PDB6V0
45	GEC0/IO104NDB6V0
46	GEB1/IO103PPB6V0
47	GEA1/IO102PPB6V0
48	GEB0/IO103NPB6V0
49	GEA0/IO102NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO101NDB5V2
56	GEA2/IO101PDB5V2
57	IO100NDB5V2
58	GEB2/IO100PDB5V2
59	IO99NDB5V2
60	GEC2/IO99PDB5V2
61	IO98PSB5V2
62	VCCIB5
63	IO96PSB5V2
64	IO94NDB5V1
65	GND
66	IO94PDB5V1
67	IO92NDB5V1
68	IO92PDB5V1
69	IO88NDB5V0
70	IO88PDB5V0
71	VCC

PQ208	
Pin Number	A3PE600 Function
72	VCCIB5
73	IO85NPB5V0
74	IO84NPB5V0
75	IO85PPB5V0
76	IO84PPB5V0
77	IO83NPB5V0
78	IO82NPB5V0
79	IO83PPB5V0
80	IO82PPB5V0
81	GND
82	IO80NDB4V1
83	IO80PDB4V1
84	IO79NPB4V1
85	IO78NPB4V1
86	IO79PPB4V1
87	IO78PPB4V1
88	VCC
89	VCCIB4
90	IO76NDB4V1
91	IO76PDB4V1
92	IO72NDB4V0
93	IO72PDB4V0
94	IO70NDB4V0
95	GDC2/IO70PDB4V0
96	IO68NDB4V0
97	GND
98	GDA2/IO68PDB4V0
99	GDB2/IO69PSB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ

FG256



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

FG256	
Pin Number	A3PE600 Function
P9	IO82PDB5V0
P10	IO76NDB4V1
P11	IO76PDB4V1
P12	VMV4
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO67NDB3V1
R1	GEA1/IO102PDB6V0
R2	GEA0/IO102NDB6V0
R3	GNDQ
R4	GEC2/IO99PDB5V2
R5	IO95NPB5V1
R6	IO91NDB5V1
R7	IO91PDB5V1
R8	IO83NDB5V0
R9	IO83PDB5V0
R10	IO77NDB4V1
R11	IO77PDB4V1
R12	IO69NDB4V0
R13	GDB2/IO69PDB4V0
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO100NDB5V2
T3	GEB2/IO100PDB5V2
T4	IO99NDB5V2
T5	IO88NDB5V0
T6	IO88PDB5V0
T7	IO89NSB5V0
T8	IO80NSB4V1
T9	IO81NDB4V1
T10	IO81PDB4V1
T11	IO70NDB4V0
T12	GDC2/IO70PDB4V0

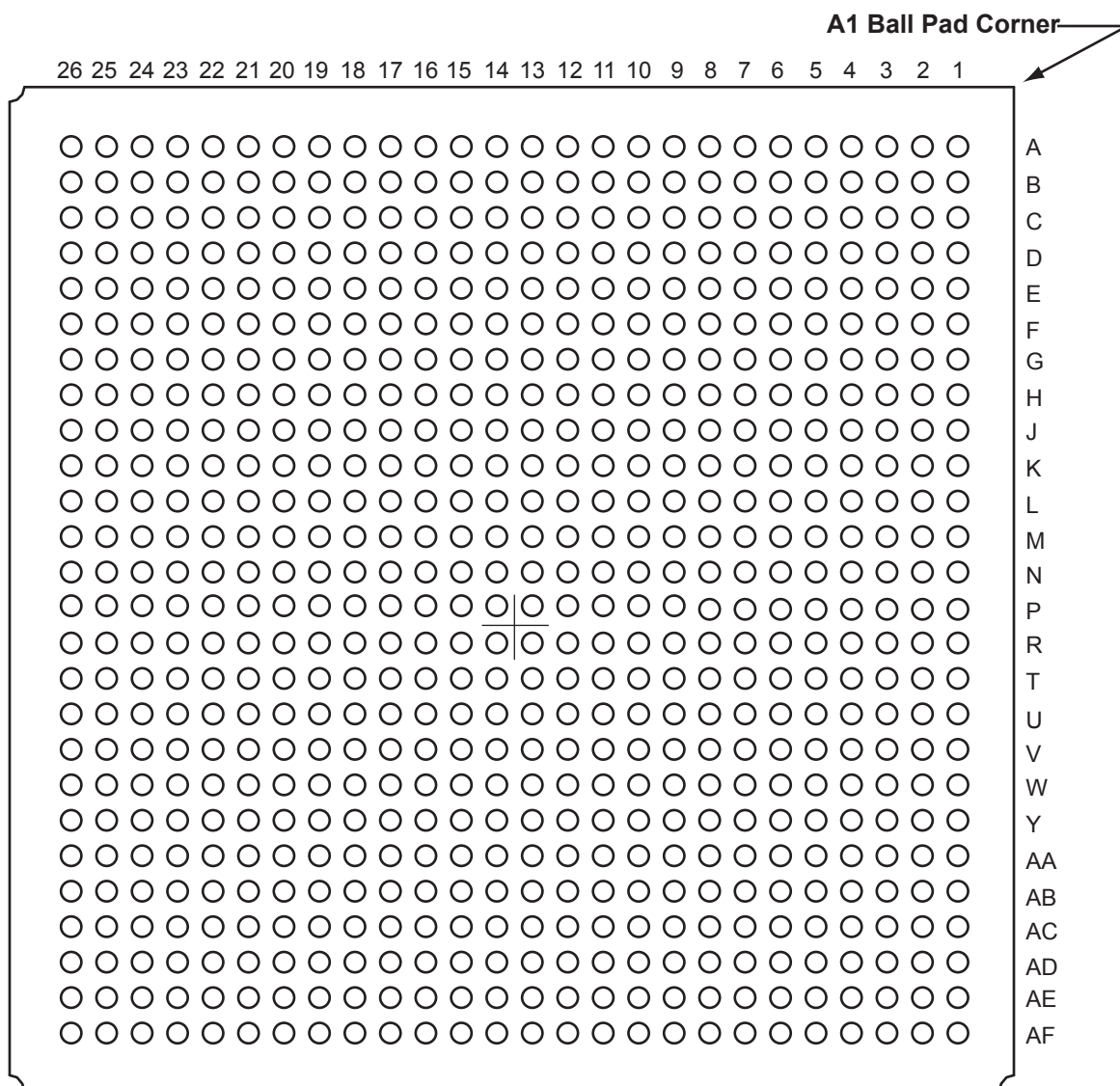
FG256	
Pin Number	A3PE600 Function
T13	IO68NDB4V0
T14	GDA2/IO68PDB4V0
T15	TMS
T16	GND

FG484	
Pin Number	A3PE600 Function
N17	IO57NPB3V0
N18	IO55NPB3V0
N19	IO57PPB3V0
N20	NC
N21	IO56NDB3V0
N22	IO58PDB3V0
P1	NC
P2	IO111PDB6V1
P3	IO115NPB6V1
P4	IO113NPB6V1
P5	IO109PPB6V0
P6	IO108PDB6V0
P7	IO108NDB6V0
P8	VCCIB6
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB3
P16	GDB0/IO66NPB3V1
P17	IO60NDB3V1
P18	IO60PDB3V1
P19	IO61PDB3V1
P20	NC
P21	IO59PDB3V0
P22	IO58NDB3V0
R1	NC
R2	IO110PDB6V0
R3	VCC
R4	IO109NPB6V0
R5	IO106NDB6V0
R6	IO106PDB6V0
R7	GEC0/IO104NPB6V0
R8	VMV5

FG484	
Pin Number	A3PE600 Function
R9	VCCIB5
R10	VCCIB5
R11	IO84NDB5V0
R12	IO84PDB5V0
R13	VCCIB4
R14	VCCIB4
R15	VMV3
R16	VCCPLD
R17	GDB1/IO66PPB3V1
R18	GDC1/IO65PDB3V1
R19	IO61NDB3V1
R20	VCC
R21	IO59NDB3V0
R22	IO62PDB3V1
T1	NC
T2	IO110NDB6V0
T3	NC
T4	IO105PDB6V0
T5	IO105NDB6V0
T6	GEC1/IO104PPB6V0
T7	VCOMPLE
T8	GNDQ
T9	GEA2/IO101PPB5V2
T10	IO92NDB5V1
T11	IO90NDB5V1
T12	IO82NDB5V0
T13	IO74NDB4V1
T14	IO74PDB4V1
T15	GNDQ
T16	VCOMPLD
T17	VJTAG
T18	GDC0/IO65NDB3V1
T19	GDA1/IO67PDB3V1
T20	NC
T21	IO64PDB3V1
T22	IO62NDB3V1

FG484	
Pin Number	A3PE600 Function
U1	NC
U2	IO107PDB6V0
U3	IO107NDB6V0
U4	GEB1/IO103PDB6V0
U5	GEB0/IO103NDB6V0
U6	VMV6
U7	VCCPLE
U8	IO101NPB5V2
U9	IO95PPB5V1
U10	IO92PDB5V1
U11	IO90PDB5V1
U12	IO82PDB5V0
U13	IO76NDB4V1
U14	IO76PDB4V1
U15	VMV4
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO67NDB3V1
U20	NC
U21	IO64NDB3V1
U22	IO63PDB3V1
V1	NC
V2	NC
V3	GND
V4	GEA1/IO102PDB6V0
V5	GEA0/IO102NDB6V0
V6	GNDQ
V7	GEC2/IO99PDB5V2
V8	IO95NPB5V1
V9	IO91NDB5V1
V10	IO91PDB5V1
V11	IO83NDB5V0
V12	IO83PDB5V0
V13	IO77NDB4V1
V14	IO77PDB4V1

FG676



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.